Gate resistor installed
Dual N-channel MOSFET

KFCAB21770L
Data Sheet

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1. GENERAL DESCRIPTION

Gate resistor installed Dual N-channel MOSFET
For lithium-ion secondary battery protection circuits

2. FEATURES

- Source-source ON resistance: RSS (on) typ. = 2.0 mΩ (VGS = 3.8 V)
- Gate-source Leakage Current: IGSS typ. = 65 nA (VGS = 8.0 V)
- CSP (Chip Size Package)
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL: Level 1)

3. MARKING SYMBOL: YT

4. PACKAGING

Embossed type (Thermo-compression sealing): 8,000 pcs / reel (standard)

5. ABSOLUTE MAXIMUM RATINGS Ta = 25 °C

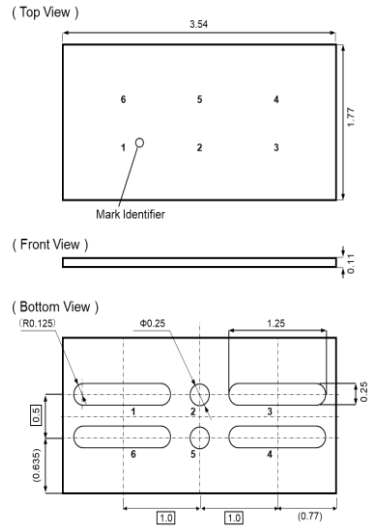
Parameter		Symbol	Rating	Unit
Source-source Voltage		VSS	12	V
Gate-source Voltage		VGS	±8	V
Source Current	DC	IS1 *1	14.5	A
		IS2 *2	27.2	
		IS3 *3	35.4	
	Pulsed *4	ISp	145	
Total Power Dissipation	DC	PD1 *1	0.54	W
		PD2 *2	1.9	
		PD3 *3	3.2	
Channel Temperature		Tch	150	°C
Storage Temperature Range		Tstg	-55 to +150	°C

6. THERMAL CHARACTERISTICS Ta = 25 °C

Parameter	Symbol	Rating	Unit
Thermal Resistance (ch-a)	Rth *1	232	°C / W
	Rth *2	66	
	Rth *3	39	

Note *1 Mounted on FR4 board (25.4 mm x 25.4 mm x t1.0 mm)
FR4 board partially covered with copper pad (23 mm^2 area, 36 μm thickness).
*2 Mounted on FR4 board (25.4 mm x 25.4 mm x t1.0 mm).
FR4 board fully covered with copper pad (602 mm^2 area, 36 μm thickness).
*3 Mounted on ceramic board (70 mm x 70 mm x t1.0 mm).
*4 t = 10 μs, Duty Cycle ≤ 1 %

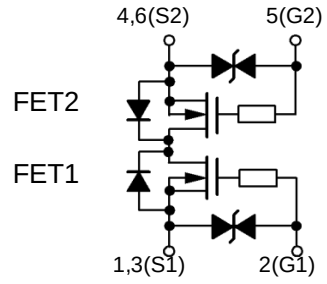
Unit: mm



1,3. Source1 (FET1) 2. Gate1 (FET1)
4,6. Source2 (FET2) 5. Gate2 (FET2)

Package	TCSP1835011-N3
JEITA	-
Code	-

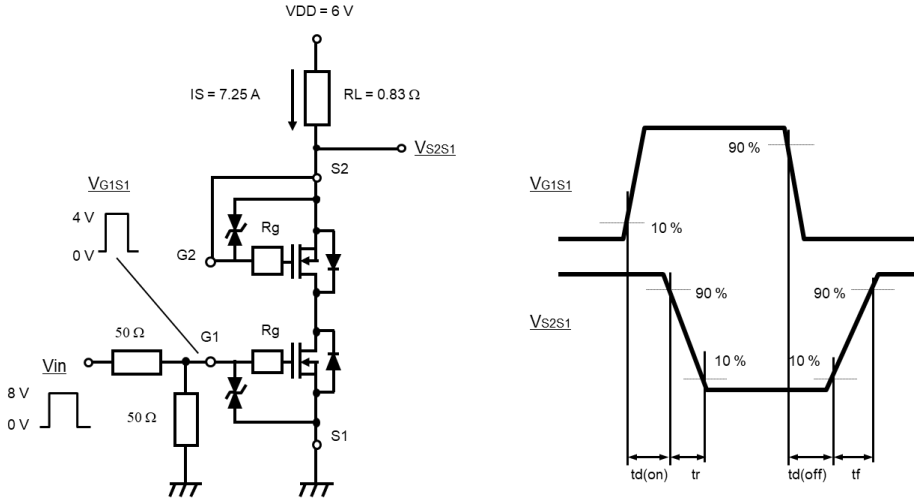
Equivalent circuit



7. ELECTRICAL CHARACTERISTICS Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Source-source Breakdown Voltage	VSSS	IS = 1 mA, VGS = 0 V	12			V
Zero Gate Voltage Source Current	ISSS	VSS = 12 V, VGS = 0 V			1.0	μA
Gate-source Leakage Current	IGSS	VGS = ±8.0 V, VSS = 0 V		±65	±120	μA
Gate-source Threshold Voltage	Vth	IS = 1.61 mA, VSS = 6 V	0.35	0.90	1.40	V
Source-source On-state Resistance	RSS(on)1	IS = 7.25 A, VGS = 4.5 V	1.30	1.80	2.35	mΩ
	RSS(on)2	IS = 7.25 A, VGS = 3.8 V	1.35	2.00	2.55	
	RSS(on)3	IS = 7.25 A, VGS = 3.1 V	1.40	2.20	3.60	
	RSS(on)4	IS = 7.25 A, VGS = 2.5 V	1.60	2.70	5.30	
Body Diode Forward Voltage	VF(s-s)	IF = 7.25 A, VGS = 0 V		0.7	1.2	V
Input Capacitance *1	Ciss	VSS = 10 V, VGS = 0 V, f = 1 kHz		4930		pF
Output Capacitance *1	Coss			740		
Reverse Transfer Capacitance *1	Crss			640		
Turn-on Delay Time *1,*2	td(on)	VDD = 6 V, VGS = 0 to 4 V IS = 7.25 A		1.8		μs
Rise Time *1,*2	tr			3.3		
Turn-off Delay Time *1,*2	td(off)	VDD = 6 V, VGS = 4 to 0 V IS = 7.25 A		5.9		μs
Fall Time *1,*2	tf			4.2		
Total Gate Charge *1	Qg	VDD = 6 V VGS = 0 to 4 V IS = 14.5 A		42		nC
Gate-source Charge *1	Qgs			14		
Gate-drain Charge *1	Qgd			7		

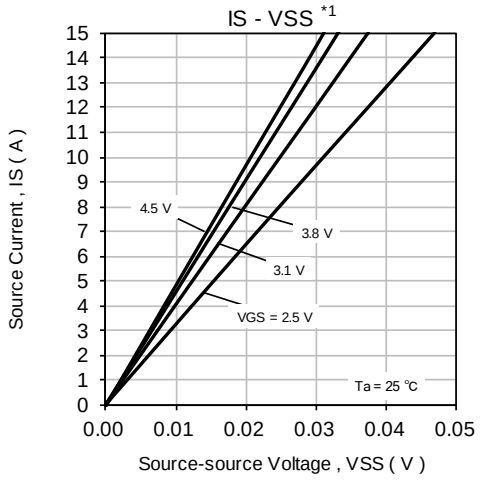
Note Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.
*1 Guaranteed by design, not subject to production testing
*2 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time

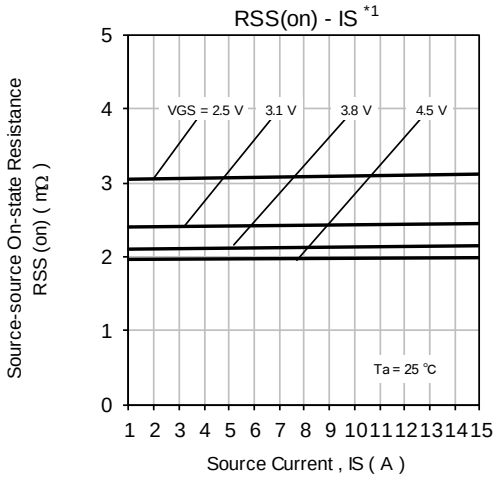


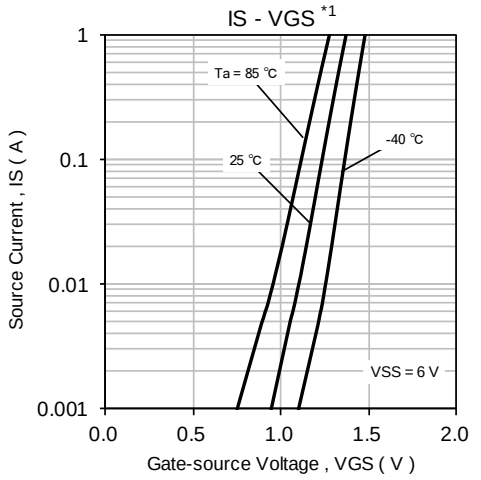
8. ELECTROSTATIC DISCHARGE CHARACTERISTICS Ta = 25 °C ± 3 °C

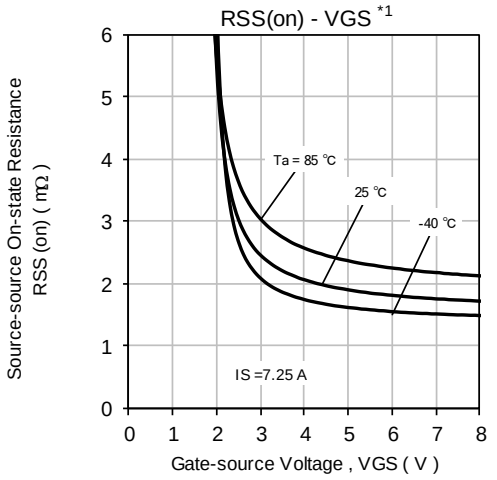
Standard	Test Type	Symbol	Conditions	Class	Value	Unit
AEC-Q101-001	Human Body Model	HBM	C = 100 pF, R = 1.5 kΩ	H1C	> 1 to ≤ 2	kV

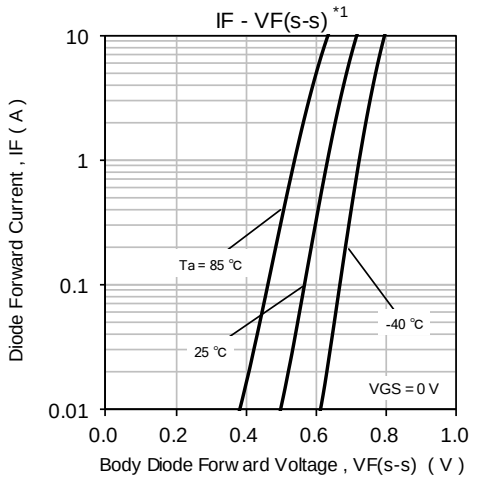
9. TECHNICAL DATA (Reference)

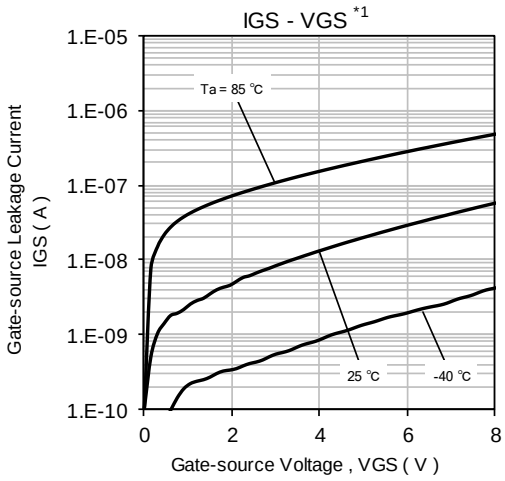




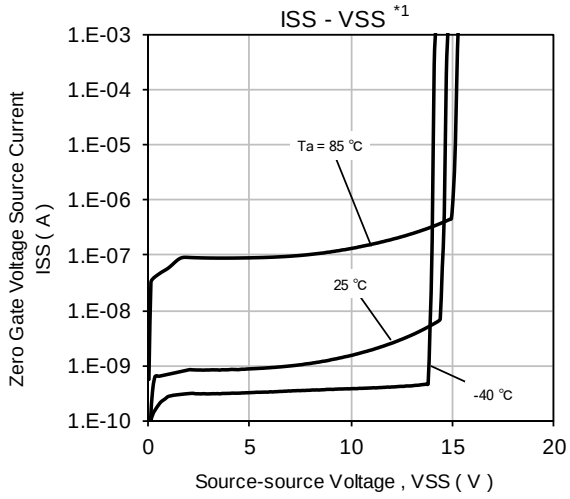


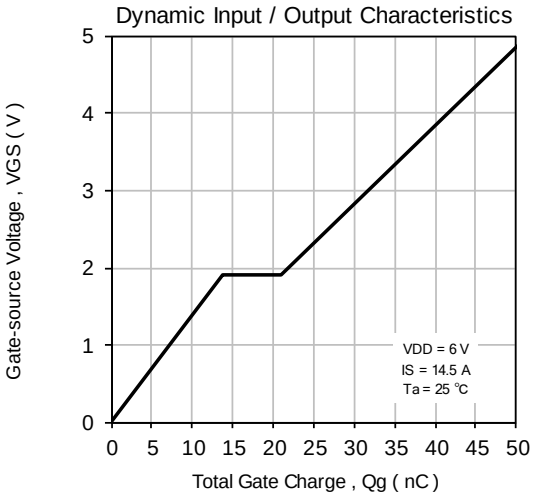


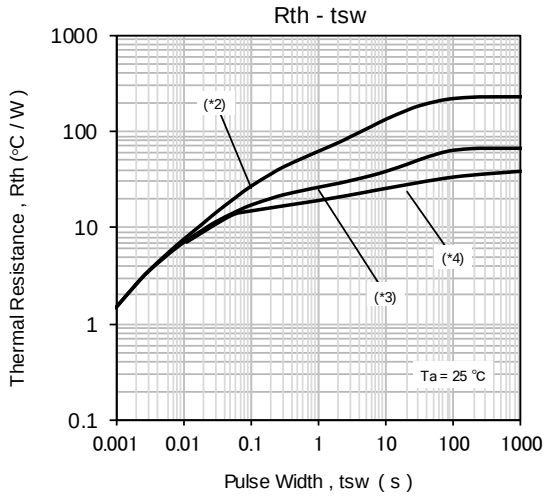


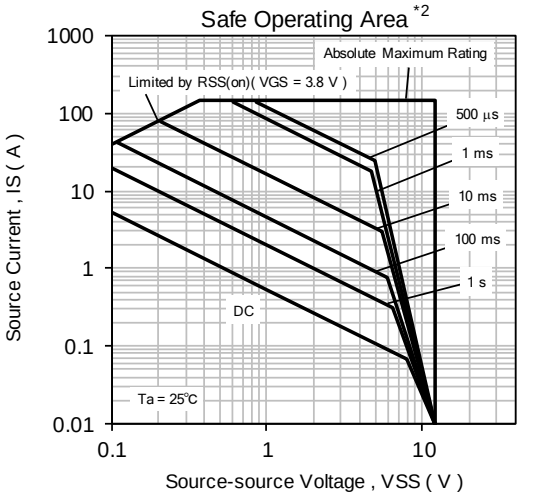


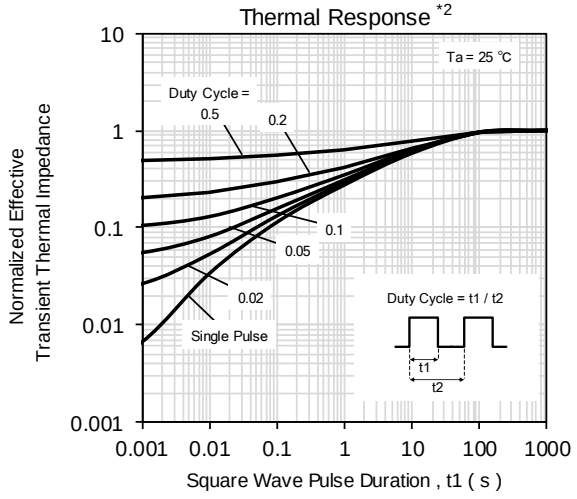
TECHNICAL DATA (Reference)











Note

*1 Pulse measurement.

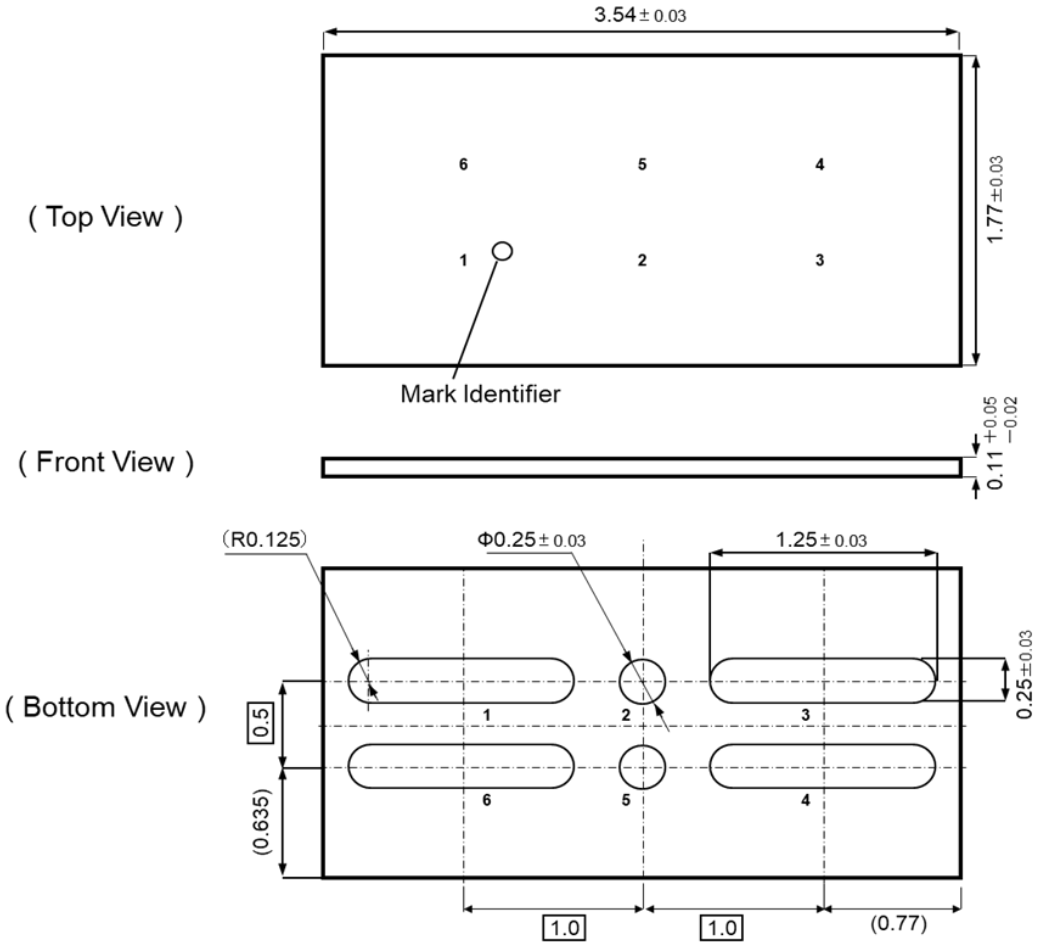
*2 Mounted on FR4 board (25.4 mm × 25.4 mm × t1.0 mm).
FR4 board partially covered with copper pad
(23 mm^2 area, 36 µm thickness).

*3 Mounted on FR4 board (25.4 mm × 25.4 mm × t1.0 mm).
FR4 board fully covered with copper pad
(602 mm^2 area, 36 µm thickness).

*4 Mounted on Ceramic board (70 mm × 70 mm × t1.0 mm).

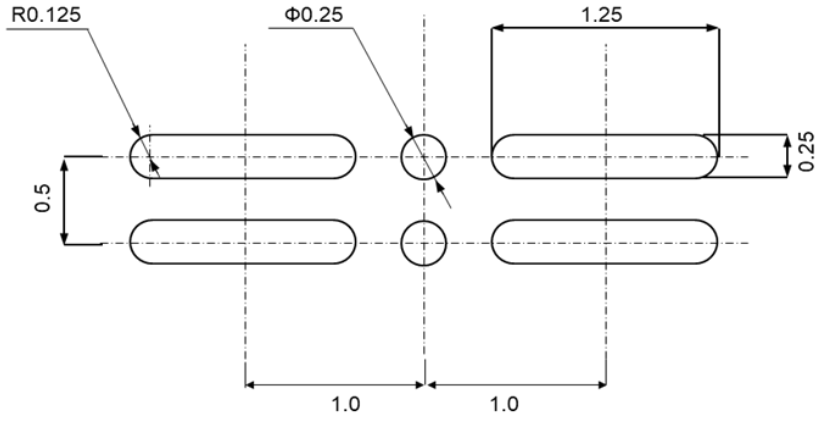
10. OUTLINE

Unit : mm



11. LAND & STENCIL PATTERN (Reference)

Unit : mm



12. REVISION HISTORY

Date	Revision	Description
2021.2.3	1.00	1. initially issued.

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